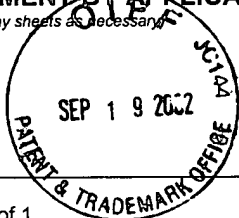


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Sheet 1 of 1

Complete if Known

Application Number	09/483881
Filing Date	January 18, 2000
First Named Inventor	Ahn, Kie
Group Art Unit	2812
Examiner Name	Unknown

Attorney Docket No: 00303.672US1

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DATE CONSIDERED

10-19-02

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